

AMENDMENTS

Please amend the application as indicated hereafter.

In the Specification

Please substitute the following clean copy text for the paragraph beginning on page 2, line 23:

431
To prevent ESD from damaging semiconductor circuits, various protective schemes may be employed. Large-scale protective schemes are often used to protect system level equipment. Examples of these schemes include, but are not limited to, the following: electrical grounding of cases and external surfaces of the electrical equipment; electrical grounding of technicians via wrist bands; the prevention of electrostatic build-up through the use of static-safe clothing static control shoes and high humidification; and the use of specialized shipping containers and bags. All of the above methods help to prevent the build-up of static charge. Additionally, small-scale, chip specific, approaches may be used. Often, high-current clamping devices are placed on the pins of a chip so that the high currents associated with an ESD event are safely shunted away from the circuitry.

Please substitute the following clean copy text for the paragraph beginning on page 4, line 5:

432
Because ESD protection is just as important for high-frequency circuits as it is for lower-frequency circuits, there is a need for an on-chip ESD protection circuit that operates without adversely affecting the performance of the high-frequency circuit.

Please substitute the following clean copy text for the paragraph beginning on page 6, line 7:

433 In Figure 1, the capacitance, C_{be} , between the base 208 and the emitter 204, is indicated by capacitor 216. Because of the configuration of transistor 202, the value of C_{be} is approximately 10 times greater than the value of C_{js} . Thus, the high frequency performance is much improved. Thus, the response at high frequencies is greatly improved as compared to previous circuits.

Please substitute the following clean copy text for the paragraph beginning on page 6, line 12:

434 The present invention thus provides for a method for protecting a circuit from electrostatic discharges through the connection of a transistor in the reverse mode between a protected circuit and a pad coupled to the protected circuit, where the pad couples the protected circuit to, for example, a transmission line.